

40 V, N-channel Trench MOSFET

9 May 2019

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 1.5 kV HBM (class H1C)
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions   |     | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -   | 40  | V    |
| V <sub>GS</sub>   | gate-source voltage              |  |     | -20 | -   | 20  | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C                     | [1] | -   | -   | 3   | А    |
| Static chara      | octeristics                      |  |     |     |     |     |      |
| R <sub>DSon</sub> | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C |     | -   | 60  | 75  | mΩ   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

# nexperia

# 5. Pinning information

| Table 2. Pinning information |        |             |                         |                          |  |  |  |
|------------------------------|--------|-------------|-------------------------|--------------------------|--|--|--|
| Pin                          | Symbol | Description | Simplified outline      | Graphic symbol           |  |  |  |
| 1                            | G      | gate        | 3                       | D                        |  |  |  |
| 2                            | S      | source      |                         |                          |  |  |  |
| 3                            | D      | drain       | 1 2<br>TO-236AB (SOT23) | G<br>G<br>S<br>017aaa255 |  |  |  |

### 6. Ordering information

| Table 3. Ordering information |          |  |         |  |  |  |
|-------------------------------|----------|--|---------|--|--|--|
| Type number                   | Package  |  |         |  |  |  |
|                               | Name     | Description                              | Version |  |  |  |
| PMV60ENEA                     | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PMV60ENEA   | HR%             |

[1] % = placeholder for manufacturing site code

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### 8. Limiting values

#### Table 5. Limiting values

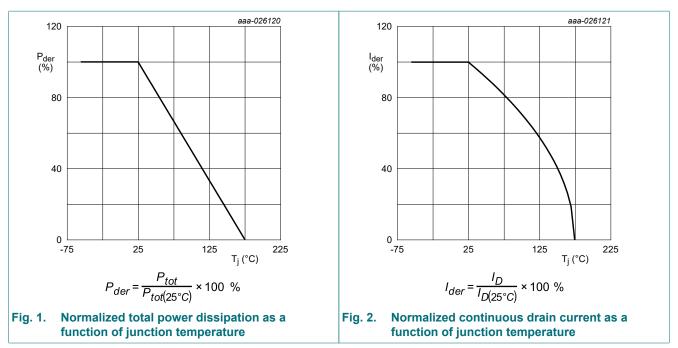
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter  | Conditions   |     | Min | Max  | Unit |
|----------------------|--|--|-----|-----|------|------|
| V <sub>DS</sub>      | drain-source voltage                             | T <sub>j</sub> = 25 °C   |     | -   | 40   | V    |
| V <sub>GS</sub>      | gate-source voltage                              |  |     | -20 | 20   | V    |
| I <sub>D</sub>       | drain current                                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C                                       | [1] | -   | 3    | А    |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C                                      | [1] | -   | 2.1  | А    |
| I <sub>DM</sub>      | peak drain current                               | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$                                  |     | -   | 12   | А    |
| P <sub>tot</sub>     | total power dissipation                          | T <sub>amb</sub> = 25 °C   | [2] | -   | 615  | mW   |
|                      |  |  | [1] | -   | 1.25 | W    |
|                      |  | T <sub>sp</sub> = 25 °C  |     | -   | 7.5  | W    |
| Tj                   | junction temperature                             |  |     | -55 | 175  | °C   |
| T <sub>amb</sub>     | ambient temperature                              |  |     | -55 | 175  | °C   |
| T <sub>stg</sub>     | storage temperature                              |  |     | -65 | 175  | °C   |
| Source-draiı         | n diode  |  |     | I   |      |      |
| Is                   | source current                                   | T <sub>amb</sub> = 25 °C   | [1] | -   | 1.3  | А    |
| ESD maximu           | um rating  |  |     | I   |      |      |
| V <sub>ESD</sub>     | electrostatic discharge voltage                  | НВМ  | [3] | -   | 1500 | V    |
| Avalanche r          | uggedness  |  |     |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche energy | T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 0.42 A; DUT in<br>avalanche (unclamped) |     | -   | 8.5  | mJ   |
|                      |  |  |     |     |      | _    |

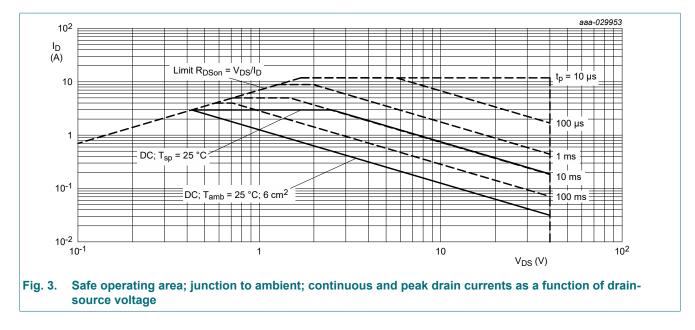
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



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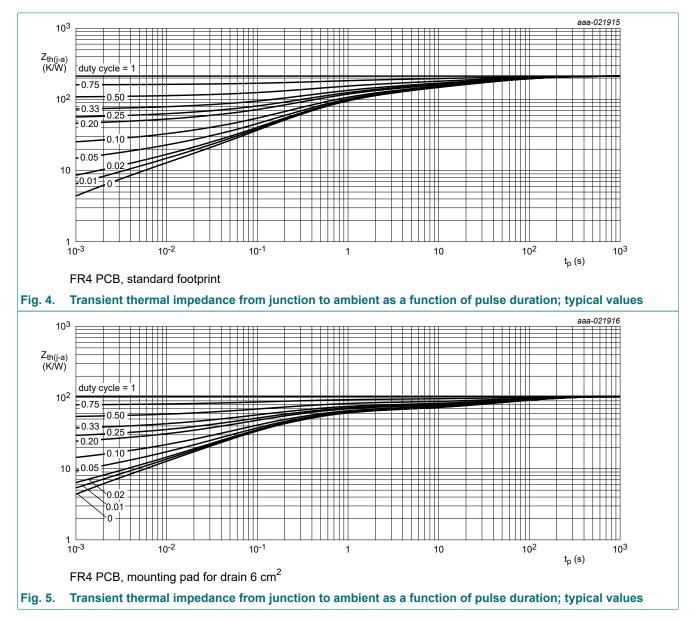


### 9. Thermal characteristics

| Symbol                                       | Parameter  | Conditions |     | Min | Тур | Мах | Unit |
|--|--|------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> thermal resistance fror | in free air                                      | [1]        | -   | 212 | 244 | K/W |      |
|  | junction to ambient                              |            | [2] | -   | 104 | 119 | K/W  |
| R <sub>th(j-sp)</sub>                        | thermal resistance from junction to solder point |            |     | -   | 17  | 20  | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

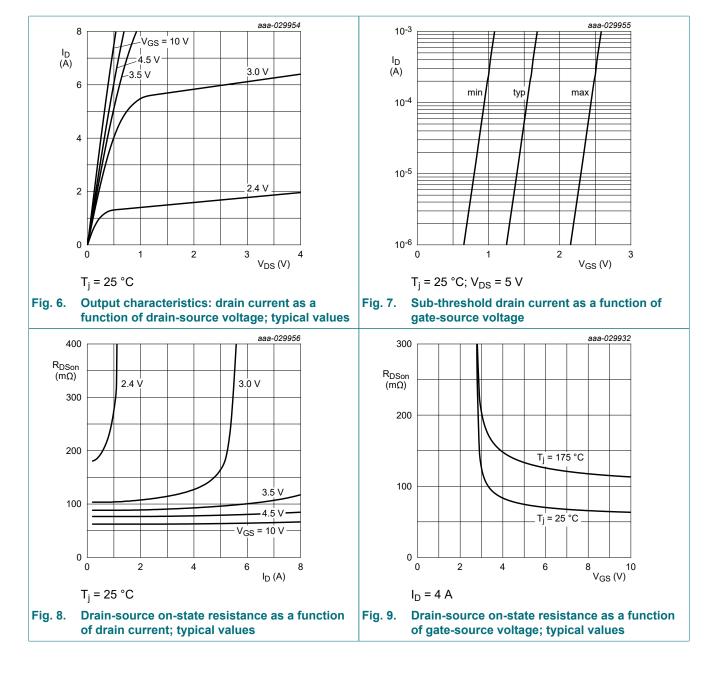
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



## **10. Characteristics**

| Symbol               | Parameter                         | Conditions  | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|---|-----|-----|-----|------|
| Static chara         | octeristics                       |   |     |     |     |      |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage | $I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$            | 40  | -   | -   | V    |
| V <sub>GSth</sub>    | gate-source threshold voltage     | I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C | 1   | 1.6 | 2.5 | V    |
| I <sub>DSS</sub>     | drain leakage current             | V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C               | -   | -   | 1   | μA   |
| I <sub>GSS</sub>     | gate leakage current              | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C               | -   | -   | 10  | μA   |
|                      |                                   | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -   | -   | -10 | μA   |
|                      |                                   | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C               | -   | -   | 2   | μA   |
|                      |                                   | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -   | -   | -2  | μA   |
| R <sub>DSon</sub>    | drain-source on-state             | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C                | -   | 60  | 75  | mΩ   |
|                      | resistance                        | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 175 °C               | -   | 114 | 143 | mΩ   |
|                      |                                   | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 2.6 A; T <sub>j</sub> = 25 °C             | -   | 75  | 99  | mΩ   |
| 9 <sub>fs</sub>      | forward<br>transconductance       | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C                | -   | 5.3 | -   | S    |
| R <sub>G</sub>       | gate resistance                   | f = 1 MHz   | -   | 2   | -   | Ω    |
| Dynamic ch           | aracteristics                     | 1   | I   |     |     |      |
| Q <sub>G(tot)</sub>  | total gate charge                 | $V_{DS}$ = 20 V; I <sub>D</sub> = 3 A; V <sub>GS</sub> = 10 V;                      | -   | 3.6 | 5   | nC   |
| Q <sub>GS</sub>      | gate-source charge                | T <sub>j</sub> = 25 °C  | -   | 0.5 | -   | nC   |
| Q <sub>GD</sub>      | gate-drain charge                 |   | -   | 0.8 | -   | nC   |
| C <sub>iss</sub>     | input capacitance                 | V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                           | -   | 180 | -   | pF   |
| C <sub>oss</sub>     | output capacitance                | T <sub>j</sub> = 25 °C  | -   | 36  | -   | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance      |   | -   | 21  | -   | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                | $V_{DS}$ = 20 V; I <sub>D</sub> = 3 A; V <sub>GS</sub> = 10 V;                      | -   | 3   | -   | ns   |
| t <sub>r</sub>       | rise time                         | R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C                                   | -   | 10  | -   | ns   |
| t <sub>d(off)</sub>  | turn-off delay time               |   | -   | 8   | -   | ns   |
| t <sub>f</sub>       | fall time                         |   | -   | 3   | -   | ns   |
| Source-drai          | n diode                           | · · ·   | 1   |     |     |      |
| V <sub>SD</sub>      | source-drain voltage              | I <sub>S</sub> = 1.3 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C               | -   | 0.8 | 1.2 | V    |
| t <sub>rr</sub>      | reverse recovery time             | I <sub>S</sub> = 0.9 A; dI <sub>S</sub> /dt = -100 A/μs;                            | -   | 8   | -   | ns   |
| Q <sub>r</sub>       | recovered charge                  | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C               | -   | 2   | -   | nC   |

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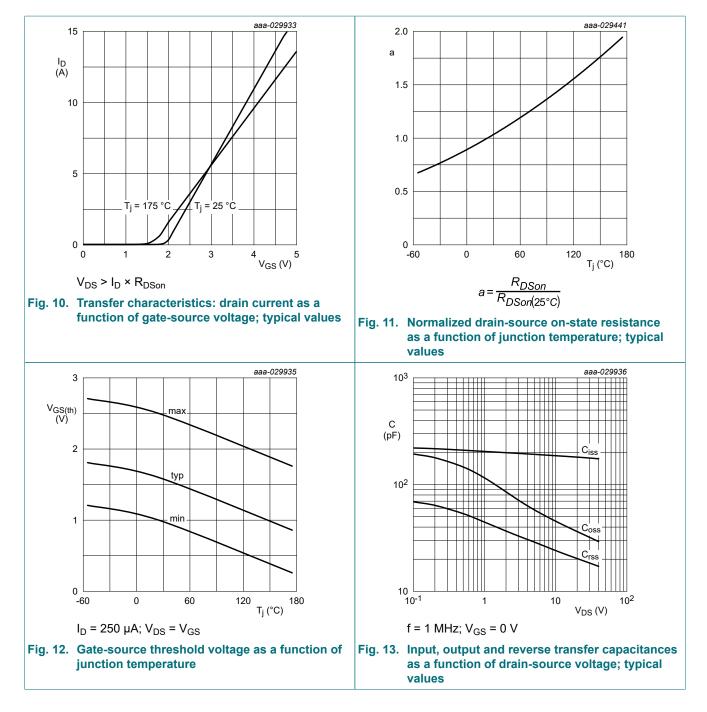


**Product data sheet** 

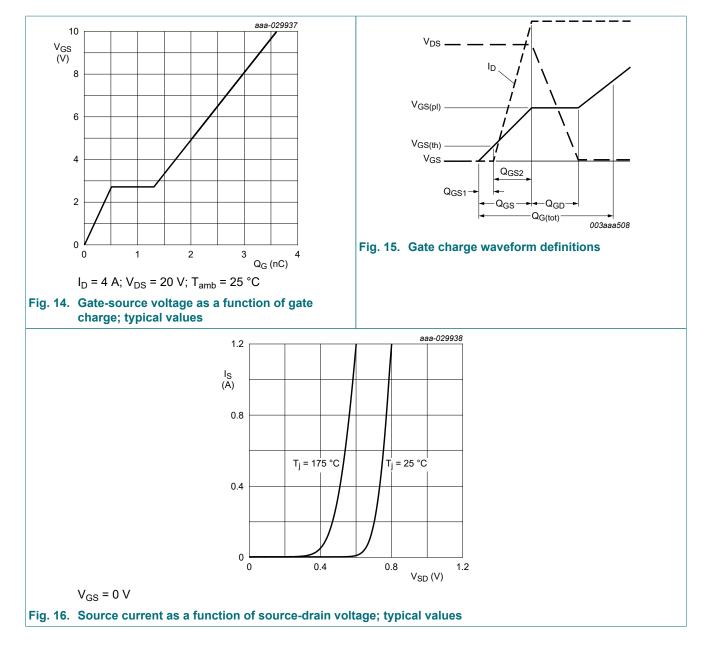
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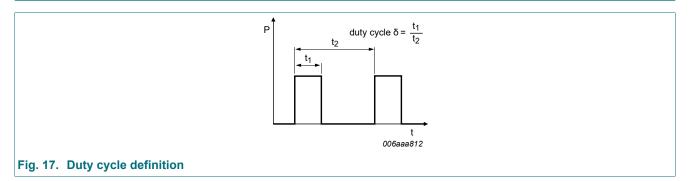
#### 40 V, N-channel Trench MOSFET



#### 40 V, N-channel Trench MOSFET



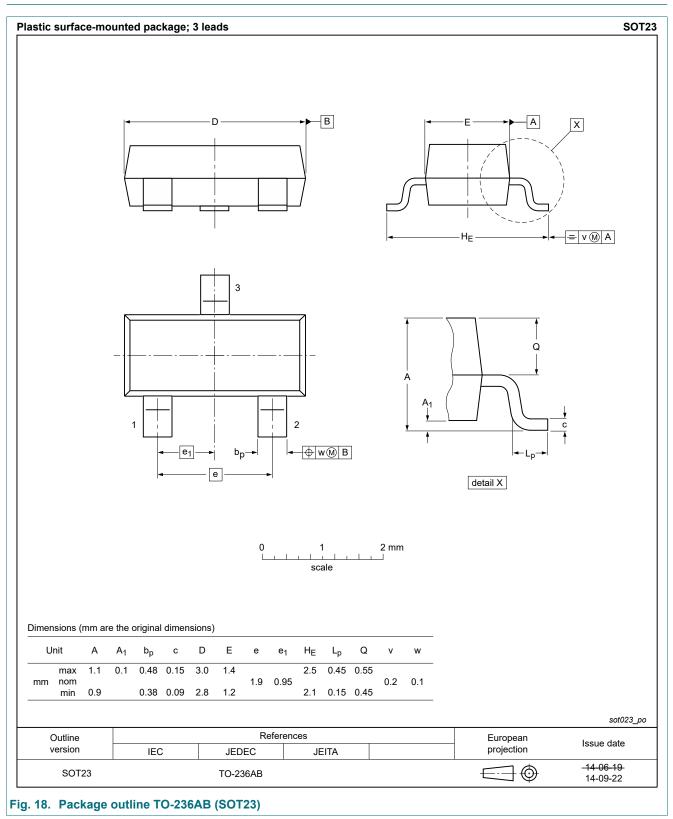
# **11. Test information**



#### **Quality information**

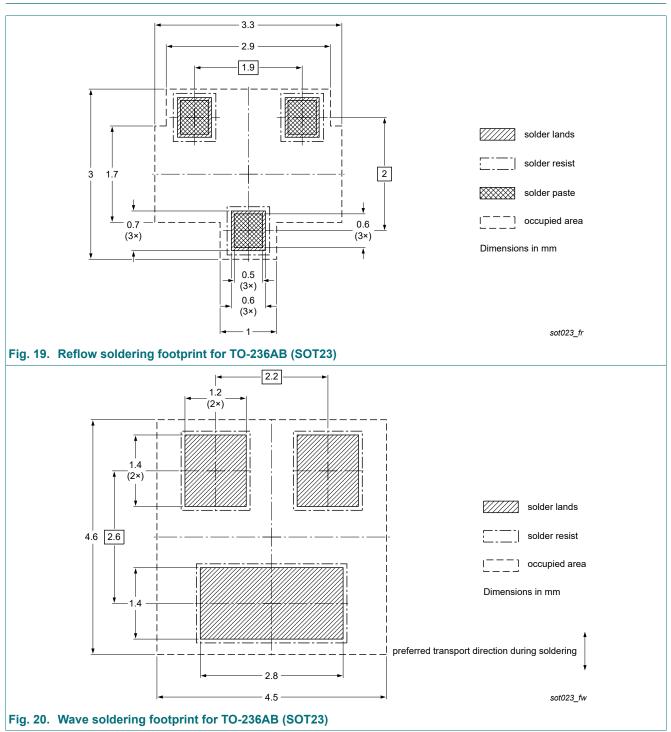
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



#### 40 V, N-channel Trench MOSFET

### 13. Soldering



# 14. Revision history

| Table 8. Revision history |              |                    |               |            |  |  |
|---------------------------|--------------|--------------------|---------------|------------|--|--|
| Data sheet ID             | Release date | Data sheet status  | Change notice | Supersedes |  |  |
| PMV60ENEA v.1             | 20190509     | Product data sheet | -             | -          |  |  |

# 15. Legal information

#### Data sheet status

| Document status [1][2]            | Product<br>status [3] | Definition  |
|-----------------------------------|-----------------------|---|
| Objective [short]<br>data sheet   | Development           | This document contains data from<br>the objective specification for<br>product development. |
| Preliminary [short]<br>data sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product [short]<br>data sheet     | Production            | This document contains the product specification.   |

 Please consult the most recently issued document before initiating or completing a design.

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